PDTC143E series

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

Rev. 10 — 8 December 2011

Product data sheet

1. Product profile

1.1 General description

NPN Resistor-Equipped Transistor (RET) family in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

| Type number | Package | | | PNP | Package |
|-------------|---------|--------|----------|------------|----------------------|
| | NXP | JEITA | JEDEC | complement | configuration |
| PDTC143EE | SOT416 | SC-75 | - | PDTA143EE | ultra small |
| PDTC143EM | SOT883 | SC-101 | - | PDTA143EM | leadless ultra small |
| PDTC143ET | SOT23 | - | TO-236AB | PDTA143ET | small |
| PDTC143EU | SOT323 | SC-70 | - | PDTA143EU | very small |

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Digital applications in automotive and industrial segments
- Control of IC inputs

- Cost-saving alternative for BC847/857 series in digital applications
- Switching loads

1.4 Quick reference data

Table 2. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------|---------------------------|------------|-----|-----|-----|------|
| V_{CEO} | collector-emitter voltage | open base | - | - | 50 | V |
| Io | output current | | - | - | 100 | mA |
| R1 | bias resistor 1 (input) | | 3.3 | 4.7 | 6.1 | kΩ |
| R2/R1 | bias resistor ratio | | 0.8 | 1 | 1.2 | |



2. Pinning information

Table 3. **Pinning** Simplified outline **Graphic symbol** Pin Description SOT23; SOT323; SOT416 1 input (base) 3 2 GND (emitter) 3 output (collector) 006aaa144 sym007 **SOT883** 1 input (base) 2 GND (emitter) output (collector) Transparent

3. Ordering information

Table 4. Ordering information

| Type number | Package | | | | | |
|-------------|---------|---------------------------------------------------------------------------------------------|---------|--|--|--|
| | Name | Description | Version | | | |
| PDTC143EE | SC-75 | plastic surface-mounted package; 3 leads | SOT416 | | | |
| PDTC143EM | SC-101 | leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm | SOT883 | | | |
| PDTC143ET | - | plastic surface-mounted package; 3 leads | SOT23 | | | |
| PDTC143EU | SC-70 | plastic surface-mounted package; 3 leads | SOT323 | | | |

4. Marking

Table 5. Marking codes

| Type number | Marking code ^[1] |
|-------------|-----------------------------|
| PDTC143EE | 02 |
| PDTC143EM | E1 |
| PDTC143ET | *02 |
| PDTC143EU | *02 |

[1] * = placeholder for manufacturing site code

5. Limiting values

Table 6. Limiting values

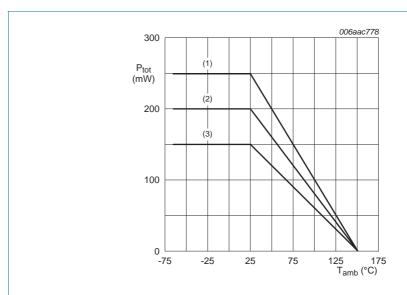
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|---------------------------|--------------------------------------|--------|------|------|
| V_{CBO} | collector-base voltage | open emitter | - | 50 | V |
| V_{CEO} | collector-emitter voltage | open base | - | 50 | V |
| V_{EBO} | emitter-base voltage | open collector | - | 10 | V |
| VI | input voltage | | | | |
| | positive | | - | +30 | V |
| | negative | | - | -10 | V |
| I _O | output current | | - | 100 | mA |
| I _{CM} | peak collector current | single pulse; $t_p \le 1 \text{ ms}$ | - | 100 | mA |
| P _{tot} | total power dissipation | $T_{amb} \le 25 ^{\circ}C$ | | | |
| | PDTC143EE (SOT416) | | [1][2] | 150 | mW |
| | PDTC143EM (SOT883) | | [2][3] | 250 | mW |
| | PDTC143ET (SOT23) | | [1] - | 250 | mW |
| | PDTC143EU (SOT323) | | [1] - | 200 | mW |
| Tj | junction temperature | | - | 150 | °C |
| T _{amb} | ambient temperature | | -65 | +150 | °C |
| T _{stg} | storage temperature | | -65 | +150 | °C |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

^[3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



- (1) SOT23; FR4 PCB, standard footprint SOT883; FR4 PCB with 70 μm copper strip line, standard footprint
- (2) SOT323; FR4 PCB, standard footprint
- (3) SOT416; FR4 PCB, standard footprint

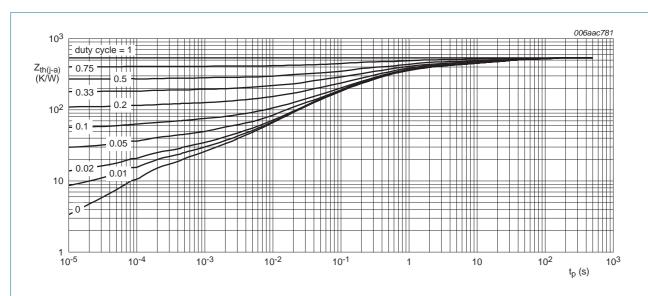
Fig 1. Power derating curves

6. Thermal characteristics

Table 7. Thermal characteristics

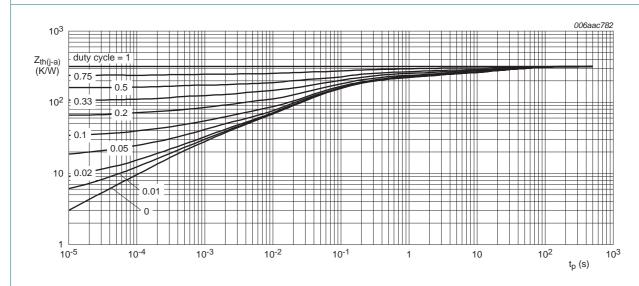
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------|---------------------------------------------|-------------|--------------|-----|-----|------|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | | | | |
| | PDTC143EE (SOT416) | | [1][2] | - | 830 | K/W |
| | PDTC143EM (SOT883) | | [2][3] | - | 500 | K/W |
| | PDTC143ET (SOT23) | | [1] - | - | 500 | K/W |
| | PDTC143EU (SOT323) | | <u>[1]</u> _ | - | 625 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



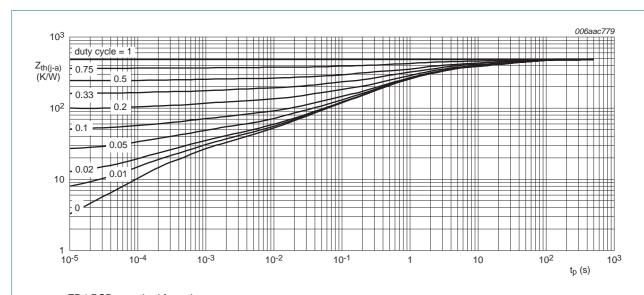
FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC143EE (SOT416); typical values



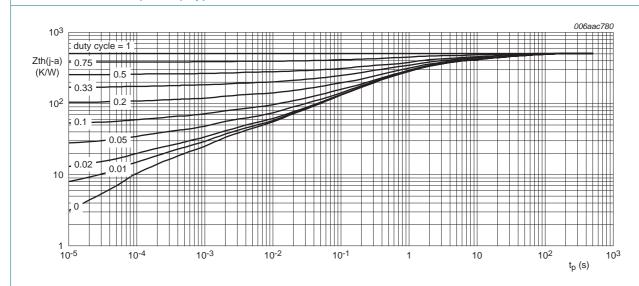
FR4 PCB, 70 µm copper strip line

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC143EM (SOT883); typical values



FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC143ET (SOT23); typical values



FR4 PCB, standard footprint

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC143EU (SOT323); typical values

NPN resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 4.7 kΩ

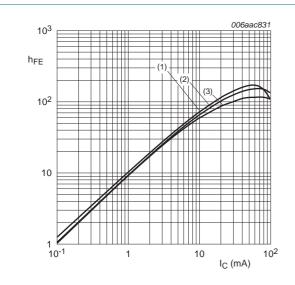
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------|--------------------------------------|---------------------------------------------------------------------------------|-------|-----|-----|------|
| I _{CBO} | collector-base cut-off current | $V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$ | - | - | 100 | nA |
| I _{CEO} | collector-emitter | $V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$ | - | - | 1 | μΑ |
| cut- | cut-off current | $V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$ | - | - | 5 | μΑ |
| I _{EBO} | emitter-base cut-off current | $V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$ | - | - | 900 | μΑ |
| h _{FE} | DC current gain | $V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}$ | 30 | - | - | |
| V_{CEsat} | collector-emitter saturation voltage | $I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$ | - | - | 150 | mV |
| $V_{I(off)}$ | off-state input voltage | $V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$ | - | 1.1 | 0.5 | V |
| $V_{I(on)}$ | on-state input voltage | $V_{CE} = 0.3 \text{ V}; I_{C} = 20 \text{ mA}$ | 2.5 | 1.9 | - | V |
| R1 | bias resistor 1 (input) | | 3.3 | 4.7 | 6.1 | kΩ |
| R2/R1 | bias resistor ratio | | 0.8 | 1 | 1.2 | |
| C _c | collector capacitance | $V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz | - | - | 2.5 | pF |
| f _T | transition frequency | $V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA;}$ f = 100 MHz | [1] _ | 230 | - | MHz |

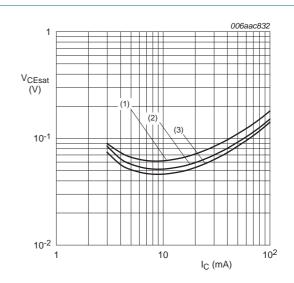
^[1] Characteristics of built-in transistor



$$V_{CE} = 5 V$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

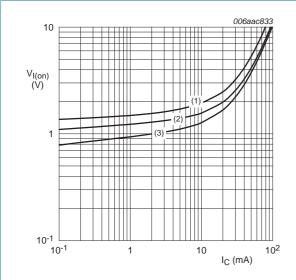
Fig 6. DC current gain as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

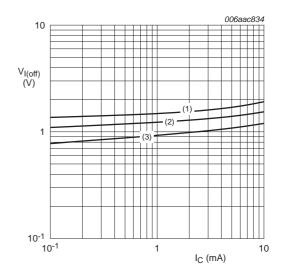
Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



$$V_{CE} = 0.3 \text{ V}$$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 8. On-state input voltage as a function of collector current; typical values



$$V_{CE} = 5 V$$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 9. Off-state input voltage as a function of collector current; typical values

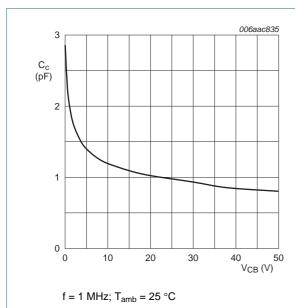


Fig 10. Collector capacitance as a function of collector-base voltage; typical values

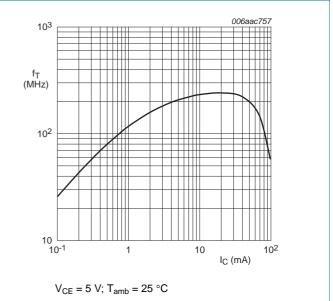


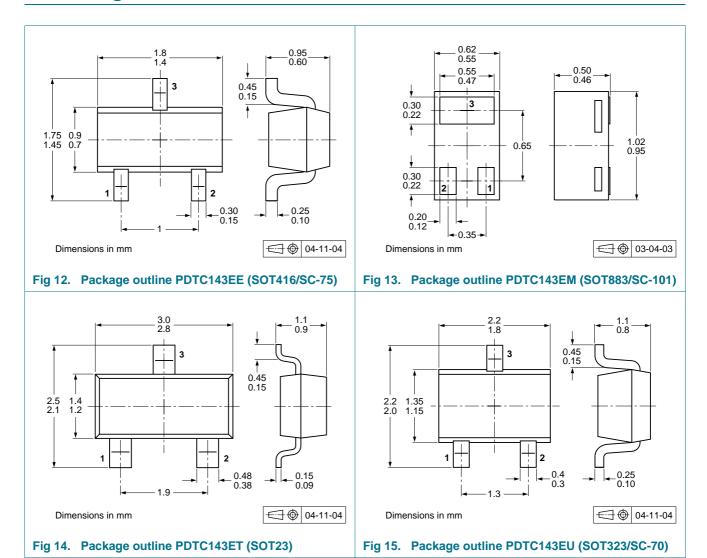
Fig 11. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

| Type number | Package | Description | Packing | Packing quantity | | |
|-------------|---------|--------------------------------|---------|------------------|-------|--|
| | | | 3000 | 5000 | 10000 | |
| PDTC143EE | SOT416 | 4 mm pitch, 8 mm tape and reel | -115 | - | -135 | |
| PDTC143EM | SOT883 | 2 mm pitch, 8 mm tape and reel | - | - | -315 | |
| PDTC143ET | SOT23 | 4 mm pitch, 8 mm tape and reel | -215 | - | -235 | |
| PDTC143EU | SOT323 | 4 mm pitch, 8 mm tape and reel | -115 | - | -135 | |

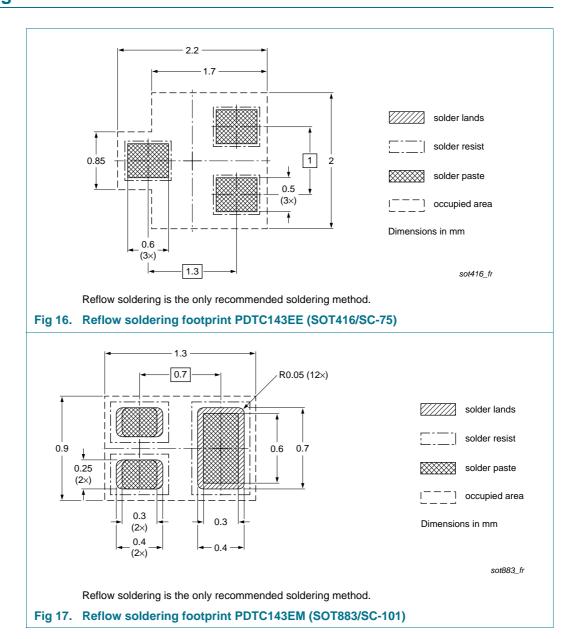
[1] For further information and the availability of packing methods, see Section 14.

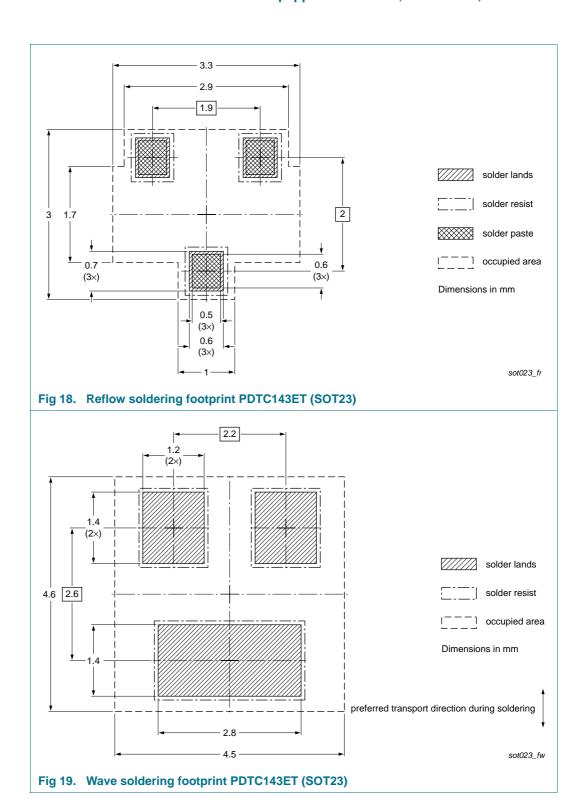
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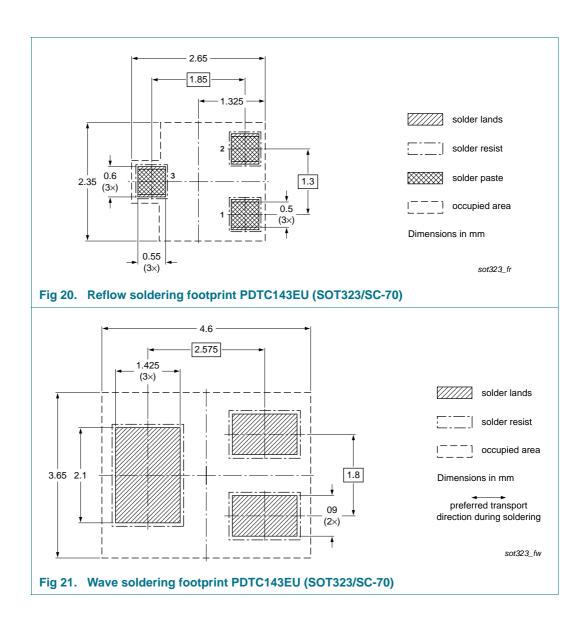
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11. Soldering







NPN resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 4.7 kΩ

12. Revision history

Table 10. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes | | | |
|---------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------------------------|---------------|---------------------|--|--|--|
| PDTC143E_SER v.10 | 20111208 | Product data sheet | - | PDTC143E_SERIES v.9 | | | |
| Modifications: | The format of this document has been redesigned to comply with the new identity guidelines of NXP Semiconductors. | | | | | | |
| | Legal texts have been adapted to the new company name where appropriate. | | | | | | |
| | Type numbers PDTC143EEF, PDTC143EK and PDTC143ES removed. | | | | | | |
| | Section 1 "Product profile": updated | | | | | | |
| | Section 4 "Marking": updated | | | | | | |
| | • Figure 1 to 11: added | | | | | | |
| | Section 6 "Thermal characteristics": updated | | | | | | |
| | <u>Table 8 "Characteristics"</u>: V_{i(on)} redefined to V_{I(on)} on-state input voltage, V_{i(off)} redefined to V_{I(off)} off-state input voltage, I_{CEO} updated, f_T added | | | | | | |
| | Section 8 "Test information": added | | | | | | |
| | Section 9 "Package outline": superseded by minimized package outline drawings | | | | | | |
| | Section 10 "Packing information": added | | | | | | |
| | Section 11 "Soldering": added | | | | | | |
| | Section 13 " | Legal information": updated | t | | | | |
| PDTC143E_SERIES v.9 | 20040805 | Product data sheet | - | PDTC143E_SERIES v.8 | | | |
| PDTC143E_SERIES v.8 | 20040318 | Product specification | - | PDTC143E_SERIES v.7 | | | |
| PDTC143E_SERIES v.7 | 20040112 | Product specification | - | PDTC143E_SERIES v.6 | | | |
| PDTC143E_SERIES v.6 | 20030910 | Product specification | - | PDTC143E_SERIES v.5 | | | |
| PDTC143E_SERIES v.5 | 20030410 | Product specification | - | - | | | |

13. Legal information

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| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---------------------------------------------------------------------------------------|
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| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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PDTC143E series

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

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PDTC143E series

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

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